L Number	Hits	Search Text	DB	Time stamp
-	46	orystal\$4 or crystallin\$4 or epitax\$4. near10 silicon adj carbide or sic and 117784-109.ccls. and partial near4 pressure	USPAT; US-PGPUE; EPO; JPO; DERWENT;	2003 (05/20 13:21
-	23	(silicon adj carbide or sic) near10 (CVD or chemical near2 vapor near2 deposit\$4	IBM_TIB USFAT; US-PGFUE;	2003:05:20 14:24
	; ;	or ale or ald or atomic adj layer adj epitam\$4 or deposit\$400 and partial near4 pressure and 117\$4.ccls.	EPO; JFC; DERWENT; IBM_TIB	
-	24	(si\$lc or sic or si near2 or near10 ratio same partial near2 pressure	USPAT; US-PGFUE; EPD; JFC; DERWENT; IBM TIB	2003105120 15:3#
:	S	ratio same partial near2 pressure same contentrat\$4 same (sid or silicon adjustration)	USFAT; US-PGFUE; EPO; JFC; DERWENT; IBM TIB	2003 05/20 14:00
_	34	same sic or silicon adj carbide:	USFAT; US-PGFUE; EPC; JFC; LEPWENT; IBM_TUB	2002 05 20 18:01
	79	contentrat\$4 near20 partial near2 pressure and 117/\$4.ccls.	USPAT; US-PGPUE; EPO; JEC; LERWENT; IBM TDE	2002/05/24
_	40	contentrat\$4 near20 partial near2 pressure and 117/84-109.ccls.	USPAT; US-PGPUB; EPC; UFC; IERWENT; IBM TDB	2003/05/24
-	27	flow near2 rate near10 ppm and 117.84-109.ccls.	USFAT; US-PGFUB; EPC; JPO; IERWENT; IBM TDB	2003/05/24 18:20
-	132	contentrat\$4 same partial near4 pressure and 117\$4.ccls.	USPAT; US-PGFUE; EPC; JFO; DEFWENT; IBM_TIB	2003/05/29 11:29
_	4	consentrat34 near5 chamber same partial near4 pressure and 117\$4.ccls.	USFAT; US-PGFUB; EPC; CFO; DERWENT; IBM TDB	2003 CE 29 11:31
	90	concentrat\$4 same partial near4 pressure same proportion\$5 near5 direct\$4	USPAT; US-PGFUB; EFO; JFC; IERWENT; IBM TIE	2003/C5/29 14:59
-	61	(silicon near3 carbide or sic) near10 superlattice	USPAT; US-PGPUE; EPO; JFC; DERWENT; IBM TDP	2003/05/29 16:35
_	34	(Silicon near3 carbide or sic) near10 (CVI) or chemical adj vapor near2 deposit\$4) and (time near10 thick\$4)) and 117,\$4.ccls.	USPAT; US-PGPUE; EFO; JFC; LERWENT; IBM TDB	2003/05.29 16:38